CHAPTER 7

$SnO₂$ dye-sensitized solar cells

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Contents

7.1 Introduction

It has been previously shown that $TiO₂$ is the most employed photoanode material in dye-sensitized solar cells (DSSCs). Despite the high surface area of $TiO₂$, it is characterized by slow electron diffusion

 $({\sim}10^{-5} \text{ cm}^2 \text{ s}^{-1})$ and lower μ_e (<1 cm² V⁻¹ s⁻¹), consequently resulting in high charge recombination at the $TiO₂/electrolyte$ interface [1]. ZnO is another widely employed photoanode material that has similar band gap (\sim 3.2 eV) to TiO₂ while providing higher μ_e than the latter. However, it is chemically unstable with the successful Ru commercial dyes due to the fact that the carboxylic group present in the dye dissolves the ZnO and creates a $\text{Zn}^{2+}/\text{dye}$ aggregate, which consequently affects the electron injection to the metal oxide semiconductor (MOS) [2,3]. Furthermore, $SnO₂$ has a lower Conduction band (CB) edge (more positively located, i.e., \sim 300-500 eV) [4-6] than TiO₂ (Fig. 7.1B) as it is made of lower energy orbitals (s orbitals) [7]. The lower CB position enables electron injection from the low-lying Lowest unoccupied molecular orbitals (LUMO) sensitizer, such as perylene dyes [9] and PbS quantum dots [10]. The incorporation of such sensitizers may lead to the utilization of the near-infrared part of the solar spectrum. Although $SnO₂$ is one of the earliest materials that showed the photovoltaic effect in the 1980s [11,12], its intrinsic lower CB (\sim 300 eV lower than TiO₂) results in routinely achieving a low $V_{\text{OC}} \sim 500 \text{ mV}$ (V_{OC} for TiO₂ $\sim 800 \text{ mV}$) despite the high $J_{SC} \ge 15 \text{ mA cm}^{-2}$. Inspired from the high μ_e of SnO₂, a number of researchers have attempted doping various transition metals to uplift its Fermi energy level; for example, Zn-doped SnO₂ resulted in a $V_{\text{OC}} \sim 780 \text{ mV}$ [13]. Various semiconductor divalent metal oxides, such as Cd, Ni, Cu, and Pb are doped in $SnO₂$ to improve its performance in DSSCs [14]. Such dopants enhanced the surface area, the dye loading, raised its flat-band potentials, and eventually enhanced the η compared to a pure SnO₂-based DSSCs. Despite these advancements, η of SnO₂-based DSSCs remains lower than that of the state-ofthe-art $TiO₂$.

Another issue with SnO₂ is its low iso-electric point (IEP) (pH \sim 4-5) compared to that of TiO₂ (pH \sim 6-7) and ZnO (pH \sim 9) [15], which makes weak bonding with the carboxylic groups upon dye anchoring, and consequently yielding low photocurrent in DSSCs. Toward this end, a number of SnO₂ morphologies other than nanoparticles (NPs), such as nanotubes (NTs), core-shell structures, and composite nanostructures are employed in DSSCs. These structures provide two advantages: (1) provide larger surface area for dye loading and (2) a directed transport path for electron diffusion. Such developments have brought $SnO₂$ to deliver η as high as \sim 4% in its pure form and 7.6% in hybrid photoanodes [16].